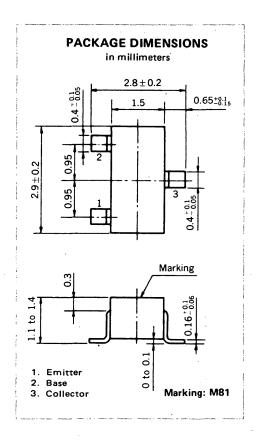


SILICON TRANSISTOR

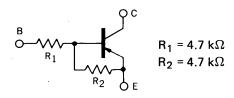
FN1L3M

MEDIUM SPEED SWITCHING RESISTOR BUILT-IN TYPE PNP TRANSISTOR MINI MOLD



FEATURES

Resistors Built-in TYPE



• Complementary to FA1L3M

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents (T_a = 25 °C) Collector to Base Voltage V_{CBO} -60 Collector to Emitter Voltage V_{CEO} -50 ٧ Emitter to Base Voltage -10 V V_{EBO} Collector Current (DC) -100Ιc mΑ Collector Current (Pulse) l_C -200mΑ Maximum Power Dissipation **Total Power Dissipation** at 25 °C Ambient Temperature Рт 200 mW Maximum Temperatures Junction Temperature 150 °C T_i °C Storage Temperature Range T_{sta} -55 to +150

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	ІСВО			-100	nA	V _{CB} = -50 V, I _E = 0
DC Current Gain	hFE1*	20	40	80		V _{CE} = -5.0 V, I _C = -5.0 mA
DC Current Gain	hFE2*	70	110			V _{CE} = -5.0 V, I _C = -50 mA
Collector Saturation Voltage	V _{CE(sat)} *		-0.08	-0.3	V	I _C = -5.0 mA, I _B = -0.25 mA
Low-Level Input Voltage	V _{IL} *		-1.1	-0.8	٧	V _{CE} = -5.0 V, 1 _C = -100 μA
High-Level Input Voltage	V _{IH} *	-3.0	-1.5		V	V _{CE} = -0.2 V, I _C = -5.0 mA
Input Resistor	R ₁	3.29	4.70	6.11	kΩ	
Resistor Ratio	R ₁ /R ₂	0.9	1.0	1.1		
Turn-on Time	ton			0.5	μs	V _{CC} = -5 V, V _{in} = -5 V R _L = 1 kΩ PW = 2 μs, Duty Cycle ≦ 2 %
Storage Time	t _{stg}			3.0	μs	
Turn-off Time	toff			5.0	μs	

^{*} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

TYPICAL CHARACTERISTICS (Ta = 25 °C)

